

TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

32,768-WORD BY 8-BIT STATIC RAM

DESCRIPTION

The TC55257DPL/DFL/DFTL/DTRL is a 262,144-bit static random access memory (SRAM) organized as 32,768 words by 8 bits. Fabricated using Toshiba's CMOS Silicon gate process technology, this device operates from a single 2.7 to 5.5 V power supply. Advanced circuit technology provides both high speed and low power at an operating current of 5 mA/MHz (typ) and a minimum cycle time of 55 ns. It is automatically placed in low-power mode at 0.3 μ A standby current (typ) when chip enable (\overline{CE}) is asserted high. There are two control inputs. \overline{CE} is used to select the device and for data retention control, and output enable (\overline{OE}) provides fast memory access. This device is well suited to various microprocessor system applications where high speed, low power and battery backup are required. The TC55257DPL/DFL/DFTL/DTRL is available in a standard plastic 28-pin dual-in-line package (DIP), plastic 28-pin small-outline package (SOP) and normal and reverse pinout plastic 28-pin thin-small-outline package (TSOP).

FEATURES

- Low-power dissipation
Operating: 27.5 mW/MHz (typical)
- Standby current of 2 μ A (maximum) at
 $T_a = 25^\circ\text{C}$
- Single power supply voltage of 2.7 to 5.5 V
- Power down features using \overline{CE} .
- Data retention supply voltage of 2 to 5.5 V
- Direct TTL compatibility for all inputs and outputs

● Access Times (maximum):

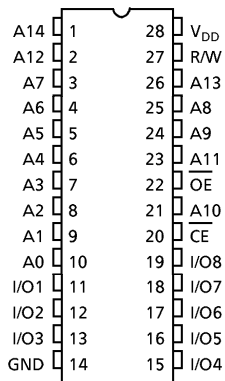
	5 V \pm 10%			2.7 to 5.5 V	
	-55V	-70V	-85V	-55V/-70V	-85V
Access Time	55 ns	70 ns	85 ns	120 ns	150 ns
\overline{CE} Access Time	55 ns	70 ns	85 ns	120 ns	150 ns
\overline{OE} Access Time	30 ns	35 ns	45 ns	70 ns	75 ns

● Packages:

- DIP28-P-600-2.54 (DPL) (Weight: 4.42 g typ)
- SOP28-P-450-1.27 (DFL) (Weight: 0.79 g typ)
- TSOP I 28-P-0.55 (DFTL) (Weight: 0.22 g typ)
- TSOP I 28-P-0.55A (DTRL) (Weight: 0.22 g typ)

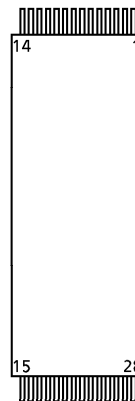
PIN ASSIGNMENT (TOP VIEW)

○ 28 PIN DIP & SOP

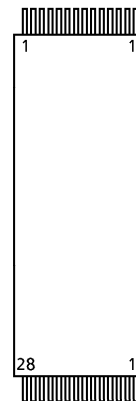


○ 28 PIN TSOP

(Normal pinout)



(Reverse pinout)



PIN NAMES

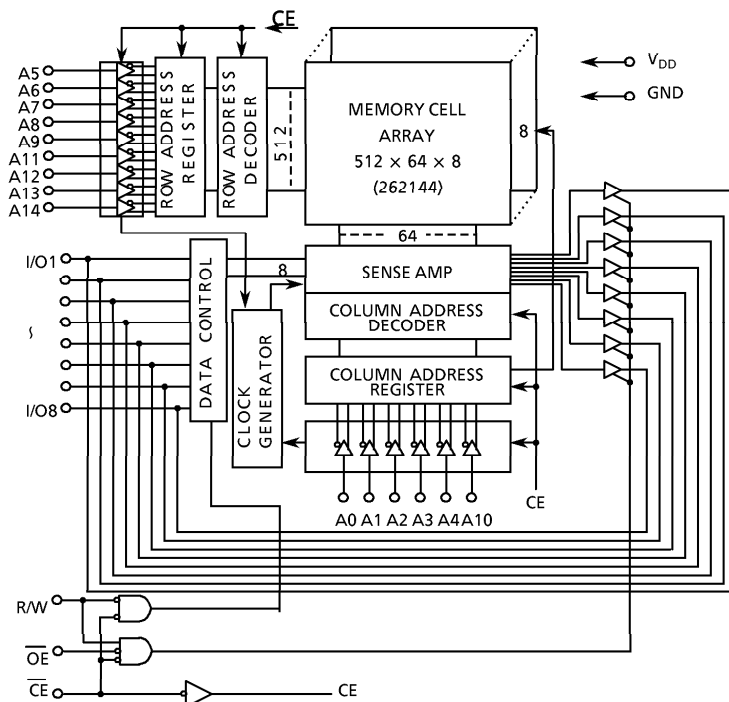
A0 to A14	Address Inputs
R/W	Read/Write Control
\overline{OE}	Output Enable
\overline{CE}	Chip Enable
I/O1 to I/O8	Data Input/Output
V_{DD}	Power
GND	Ground

PIN NO.	1	2	3	4	5	6	7	8	9	10	11	12	13	14
PIN NAME	\overline{OE}	A ₁₁	A ₉	A ₈	A ₁₃	R/W	V_{DD}	A ₁₄	A ₁₂	A ₇	A ₆	A ₅	A ₄	A ₃
PIN NO.	15	16	17	18	19	20	21	22	23	24	25	26	27	28
PIN NAME	A ₂	A ₁	A ₀	I/O1	I/O2	I/O3	GND	I/O4	I/O5	I/O6	I/O7	I/O8	\overline{CE}	A ₁₀

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BLOCK DIAGRAM



OPERATION MODE

MODE	\overline{CE}	\overline{OE}	R/W	I/O1 to I/O8	POWER
Read	L	L	H	D _{OUT}	I _{DDO}
Write	L	x	L	D _{IN}	I _{DDO}
Outputs Disabled	L	H	H	High-Z	I _{DDO}
Standby	H	x	x	High-Z	I _{DDS}

Note: x = don't care. H = logic high. L = logic low.

ABSOLUTE MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V _{DD}	Power Supply Voltage	- 0.3 to 7.0	V
V _{IN}	Input Voltage	- 0.3* to 7.0	V
V _{I/O}	Input/Output Voltage	- 0.5* to V _{DD} + 0.5	V
P _D	Power Dissipation	1.0/0.6**	W
T _{solder}	Soldering Temperature (10 s)	260	°C
T _{strg}	Storage Temperature	- 55 to 150	°C
T _{opr}	Operating Temperature	0 to 70	°C

* - 3.0 V when measured at a pulse width of 50 ns

** SOP

DC RECOMMENDED OPERATING CONDITIONS (Ta = 0° to 70°C)

SYMBOL	PARAMETER	5 V ± 10%			2.7 to 5.5 V			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
V _{DD}	Power Supply Voltage	4.5	–	5.5	2.7	–	5.5	V
V _{IH}	Input High Voltage	2.2	–	V _{DD} + 0.3	V _{DD} – 0.2	–	V _{DD} + 0.3	
V _{IL}	Input Low Voltage	– 0.3*	–	0.8	– 0.3*	–	0.2	
V _{DH}	Data Retention Supply Voltage	2.0	–	5.5	2.0	–	5.5	

* – 3.0 V when measured at a pulse width of 50 ns

DC CHARACTERISTICS (Ta = 0° to 70°C, V_{DD} = 3 V ± 10%)

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT	
I _{IL}	Input Leakage Current	V _{IN} = 0 V to V _{DD}	–	–	± 1.0	μA	
I _{OH}	Output High Current	V _{OH} = 2.4 V	– 1.0	–	–	mA	
I _{OL}	Output Low Current	V _{OL} = 0.4 V	4.0	–	–	mA	
I _{LO}	Output Leakage Current	$\overline{CE} = V_{IH}$ or R/W = V _{IL} or $\overline{OE} = V_{IH}$ V _{OUT} = 0 V to V _{DD}	–	–	± 1.0	μA	
I _{DDO1}	Operating Current	$\overline{CE} = V_{IL}$ R/W = V _{IH} Other Inputs = V _{IH} /V _{IL} I _{OUT} = 0 mA	t _{cycle} = 1 μs	–	10	–	mA
			t _{cycle} = min	–	–	70	
I _{DDO2}	Operating Current	$\overline{CE} = 0.2$ V R/W = V _{DD} – 0.2 V Other Inputs = V _{DD} – 0.2 V/0.2 V I _{OUT} = 0 mA	t _{cycle} = 1 μs	–	5	–	mA
			t _{cycle} = min	–	–	60	
I _{DDS1}	Standby Current	$\overline{CE} = V_{IH}$	–	–	3	mA	
I _{DDS2}	Standby Current	$\overline{CE} = V_{DD} - 0.2$ V	Ta = 0° to 70°C	–	–	20	μA
		V _{DD} = 2.0 to 5.5 V	Ta = 25°C	–	0.3	2	μA

DC CHARACTERISTICS ($T_a = 0^\circ$ to 70°C , $V_{DD} = 5\text{ V} \pm 10\%$)

SYMBOL	PARAMETER	TEST CONDITION		MIN	TYP	MAX	UNIT	
I_{IL}	Input Leakage Current	$V_{IN} = 0\text{ V to }V_{DD}$		-	-	± 1.0	μA	
I_{OH}	Output High Current	$V_{OH} = V_{DD} - 0.2\text{ V}$		- 0.1	-	-	mA	
I_{OL}	Output Low Current	$V_{OL} = 0.2\text{ V}$		0.1	-	-	mA	
I_{LO}	Output Leakage Current	$\overline{CE} = V_{IH}$ or $R/W = V_{IL}$ or $\overline{OE} = V_{IH}$, $V_{OUT} = 0\text{ V to }V_{DD}$		-	-	± 1.0	μA	
I_{DDO2}	Operating Current	$\overline{CE} = 0.2\text{ V}$ $R/W = V_{DD} - 0.2\text{ V}$, $I_{OUT} = 0\text{ mA}$ Other Inputs = $V_{DD} - 0.2\text{ V}/0.2\text{ V}$	Tcycle	min	-	-	20	mA
				$1\ \mu\text{s}$	-	-	5	
I_{DDs2}	Standby Current	$\overline{CE} = V_{DD} - 0.2\text{ V}$	$V_{DD} = 3\text{ V} \pm 10\%$	$T_a = 25^\circ\text{C}$	-	1	1.5	μA
				$T_a = 0^\circ$ to 70°C	-	-	15	
			$V_{DD} = 3.0\text{ V}$	$T_a = 25^\circ\text{C}$	-	-	1	
				$T_a = 0^\circ$ to 40°C	-	-	2	
	$T_a = 0^\circ$ to 70°C	-	-	10				

CAPACITANCE ($T_a = 25^\circ\text{C}$, $f = 1\text{ MHz}$)

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C_{IN}	Input Capacitance	$V_{IN} = \text{GND}$	10	pF
C_{OUT}	Output Capacitance	$V_{OUT} = \text{GND}$	10	

Note: This parameter is periodically sampled and is not 100% tested.

AC CHARACTERISTICS AND OPERATING CONDITIONS (Ta = 0° to 70°C, V_{DD} = 5 V ± 10%)

READ CYCLE

SYMBOL	PARAMETER	TC55257DPL/DFL/DFTL/DTRL						UNIT
		-55V		-70V		-85V		
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{RC}	Read Cycle Time	55	-	70	-	85	-	ns
t _{ACC}	Address Access Time	-	55	-	70	-	85	
t _{CO}	Chip Enable Access Time	-	55	-	70	-	85	
t _{OE}	Output Enable Access Time	-	30	-	35	-	45	
t _{COE}	Chip Enable Low to Output Active	10	-	10	-	10	-	
t _{OEE}	Output Enable Low to Output Active	5	-	5	-	5	-	
t _{OD}	Chip Enable High to Output High-Z	-	20	-	25	-	30	
t _{ODO}	Output Enable High to Output High-Z	-	20	-	25	-	30	
t _{OH}	Output Data Hold Time	10	-	10	-	10	-	

WRITE CYCLE

SYMBOL	PARAMETER	TC55257DPL/DFL/DFTL/DTRL						UNIT
		-55V		-70V		-85V		
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{WC}	Write Cycle Time	55	-	70	-	85	-	ns
t _{WP}	Write Pulse Width	45	-	50	-	60	-	
t _{CW}	Chip Enable to End of Write	50	-	60	-	65	-	
t _{AS}	Address Setup Time	0	-	0	-	0	-	
t _{WR}	Write Recovery Time	0	-	0	-	0	-	
t _{ODW}	R/W Low to Output High-Z	-	20	-	25	-	30	
t _{OEW}	R/W High to Output Active	5	-	5	-	5	-	
t _{DS}	Data Setup Time	25	-	30	-	40	-	
t _{DH}	Data Hold Time	0	-	0	-	0	-	

AC TEST CONDITIONS

Output load: 30 pF + one TTL gate (-55V)

100 pF + one TTL gate (-70L, -85L)

Input pulse level: 0.6 V, 2.4 V

Timing measurements: 1.5 V

Reference level: 1.5 V

t_R, t_F: 5 ns

AC CHARACTERISTICS AND OPERATING CONDITIONS (Ta = 0° to 70°C, V_{DD} = 2.7 to 5.5 V)

READ CYCLE

SYMBOL	PARAMETER	TC55257DPL/DFL/DFTL/DTRL				UNIT
		-55V/-70V		-85V		
		MIN	MAX	MIN	MAX	
t _{RC}	Read Cycle Time	120	–	150	–	ns
t _{ACC}	Address Access Time	–	120	–	150	
t _{CO}	Chip Enable Access Time	–	120	–	150	
t _{OE}	Output Enable Access Time	–	70	–	75	
t _{COE}	Chip Enable Low to Output Active	10	–	10	–	
t _{OOE}	Output Enable Low to Output Active	5	–	5	–	
t _{OD}	Chip Enable High to Output High-Z	–	50	–	50	
t _{ODO}	Output Enable High to Output High-Z	–	50	–	50	
t _{OH}	Output Data Hold Time	10	–	10	–	

WRITE CYCLE

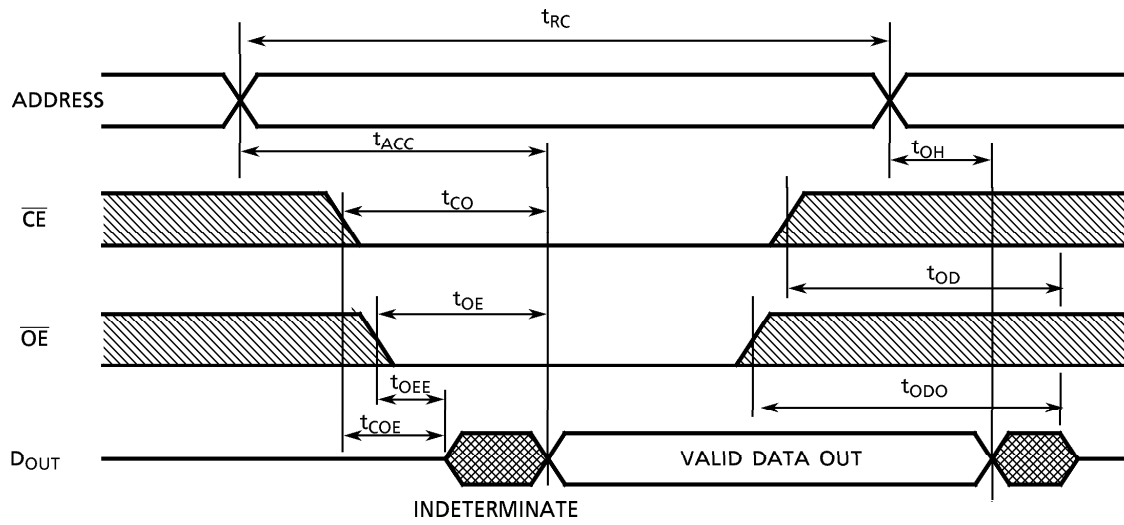
SYMBOL	PARAMETER	TC55257DPL/DFL/DFTL/DTRL				UNIT
		-55V/-70V		-85V		
		MIN	MAX	MIN	MAX	
t _{WC}	Write Cycle Time	120	–	150	–	ns
t _{WP}	Write Pulse Width	80	–	100	–	
t _{CW}	Chip Enable to End of Write	100	–	120	–	
t _{AS}	Address Setup Time	0	–	0	–	
t _{WR}	Write Recovery Time	0	–	0	–	
t _{ODW}	R/W Low to Output High-Z	–	50	–	50	
t _{OEW}	R/W High to Output Active	5	–	5	–	
t _{DS}	Data Setup Time	50	–	60	–	
t _{DH}	Data Hold Time	0	–	0	–	

AC TEST CONDITIONS

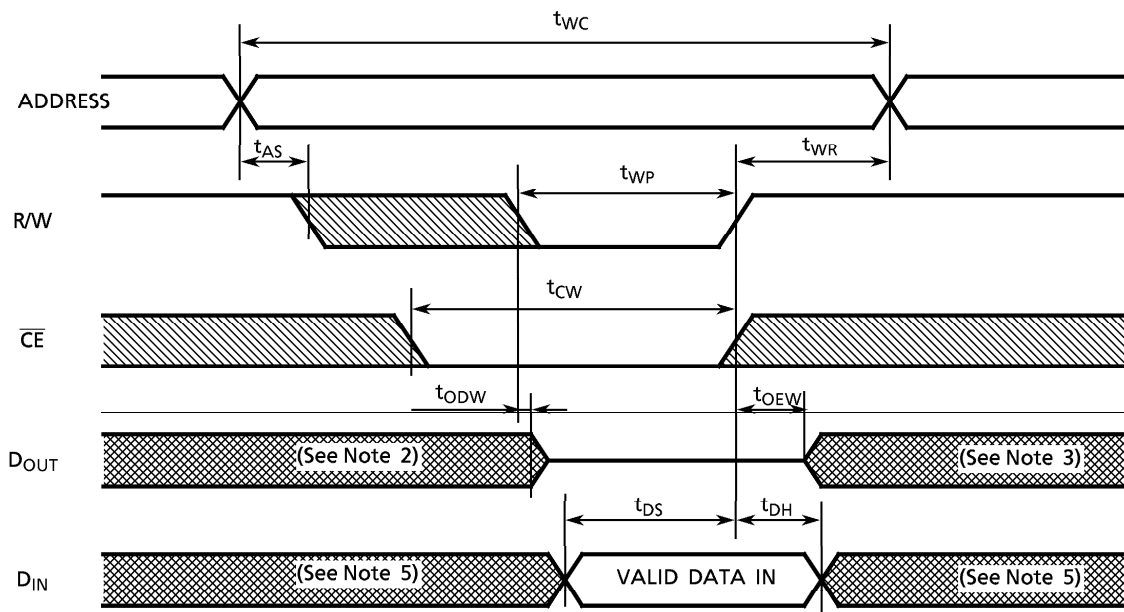
Output load: 100 pF (including jig)
 Input pulse level: 0.2 V, V_{DD} – 0.2 V
 Timing measurements: 1.5 V
 Reference level: 1.5 V
 t_R, t_F: 5 ns

TIMING DIAGRAMS

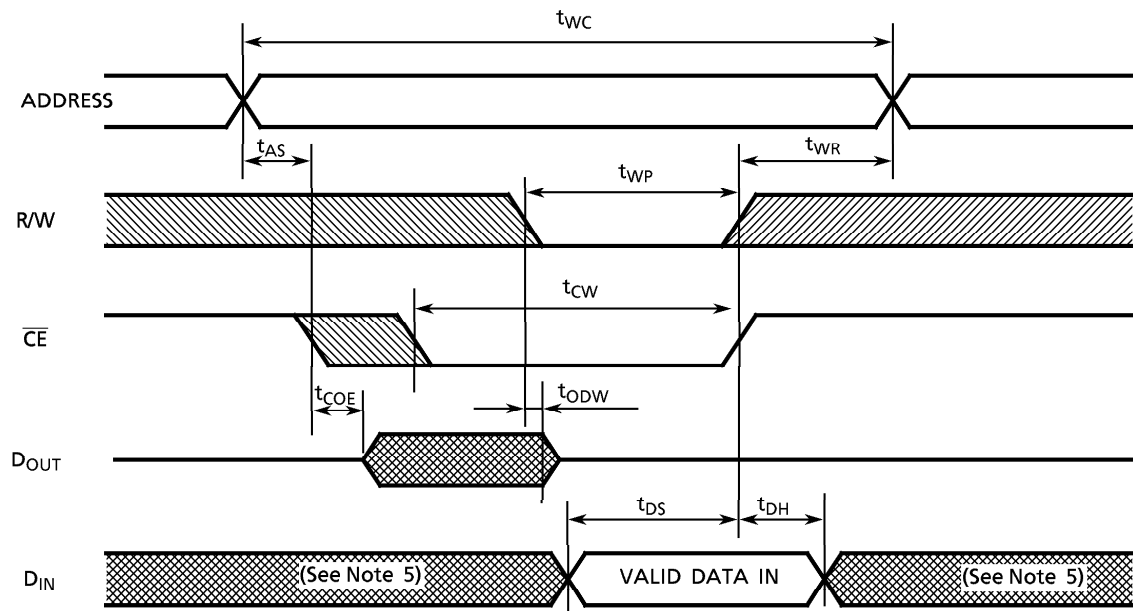
READ CYCLE (See Note 1)



WRITE CYCLE 1 (R/W CONTROLLED) (See Note 4)



WRITE CYCLE 2 (\overline{CE} CONTROLLED) (See Note 4)



Note: (1) R/W remains HIGH for the read cycle.

(2) If \overline{CE} goes LOW coincident with or after R/W goes LOW, the outputs will remain at high impedance.

(3) If \overline{CE} goes HIGH coincident with or before R/W goes HIGH, the outputs will remain at high impedance.

(4) If \overline{OE} is HIGH during the write cycle, the outputs will remain at high impedance.

(5) Because I/O signals may be in the output state at this time, input signals of reverse polarity must not be applied.

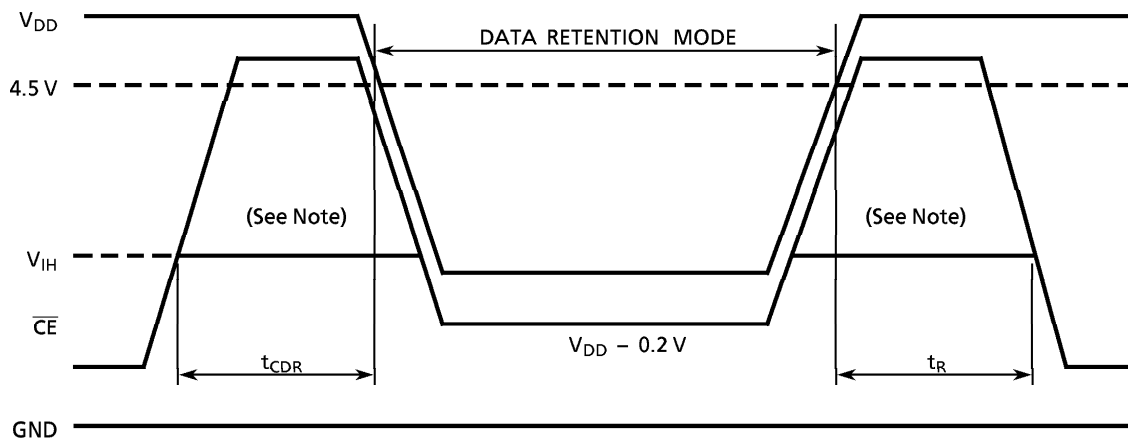
DATA RETENTION CHARACTERISTICS (Ta = 0° to 70°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V _{DH}	Data Retention Supply Voltage	2.0	–	5.5	V
I _{DDS2}	Standby Current	V _{DH} = 3.0 V	–	10*	μA
		V _{DH} = 5.5 V	–	20	
t _{CDR}	Chip Deselect to Data Retention Mode Time	0	–	–	ns
t _R	Recovery Time	t _{RC} (See Note)	–	–	

* 2 μA (max) at Ta = 0° to 40°C

Note: Read cycle time.

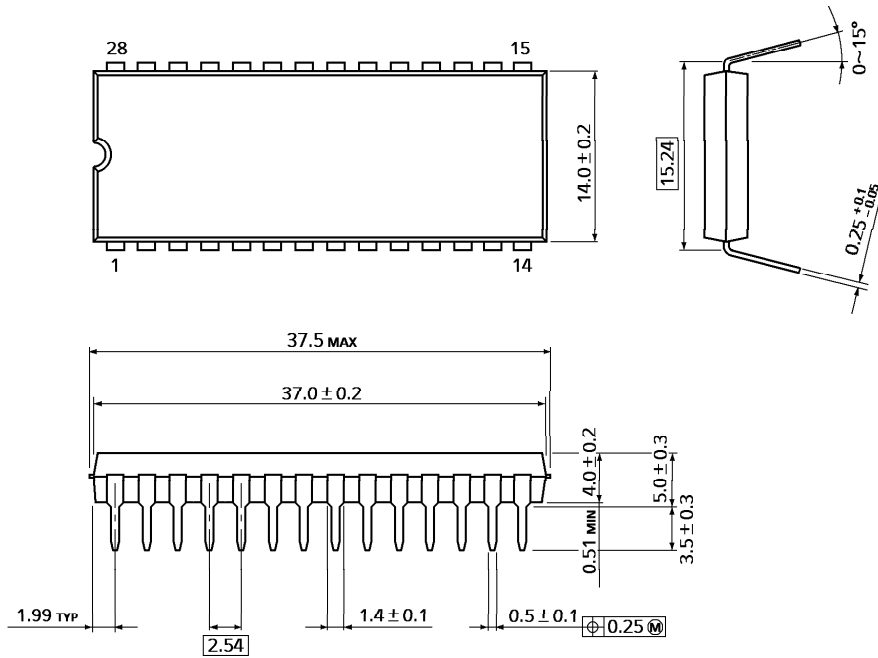
CE CONTROLLED DATA RETENTION MODE



Note: When \overline{CE} is operating at the V_{IH} level (2.2 V), the standby current is given by I_{DDS1} during the transition of V_{DD} from 4.5 to 2.4 V.

PACKAGE DIMENSIONS (DIP28-P-600-2.54)

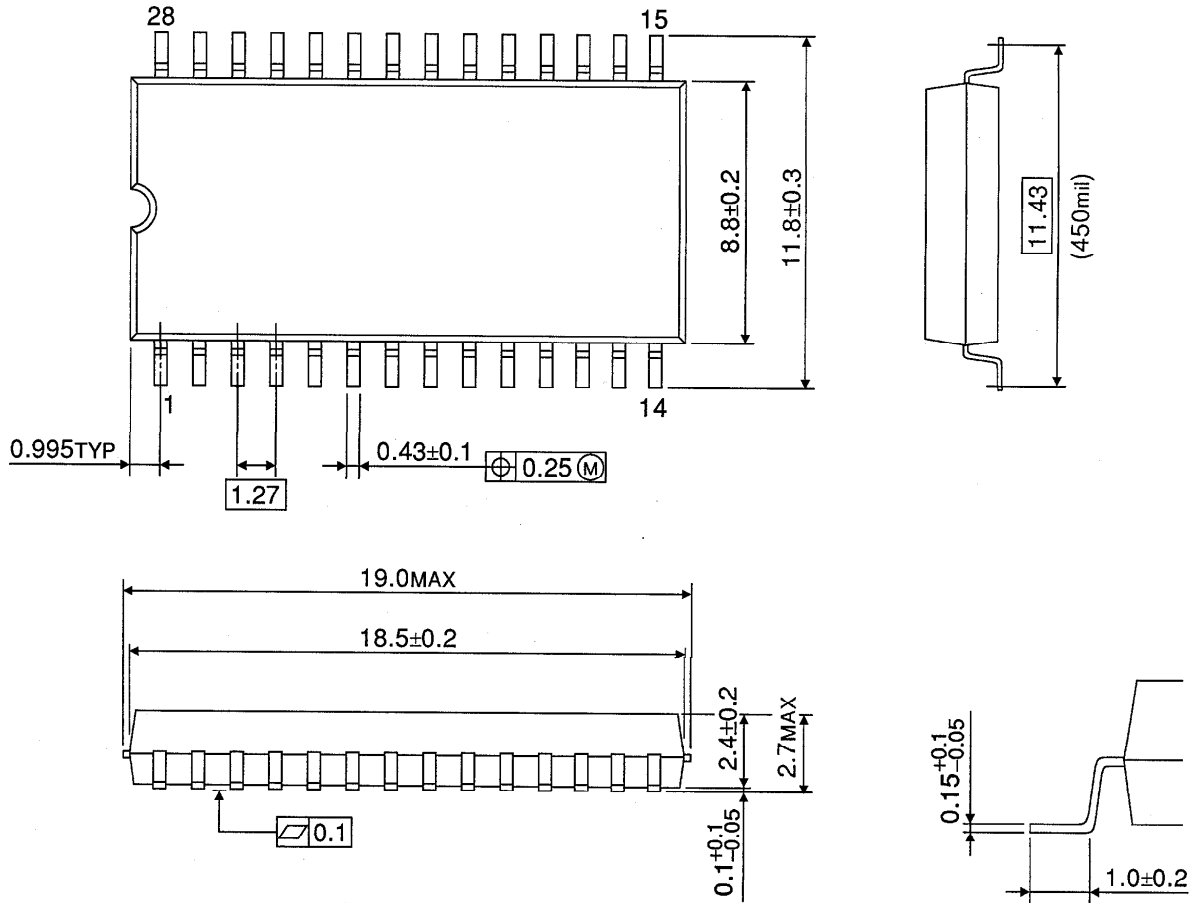
Units in mm



Weight: 4.42 g (typ)

PACKAGE DIMENSIONS (SOP28-P-450-1.27)

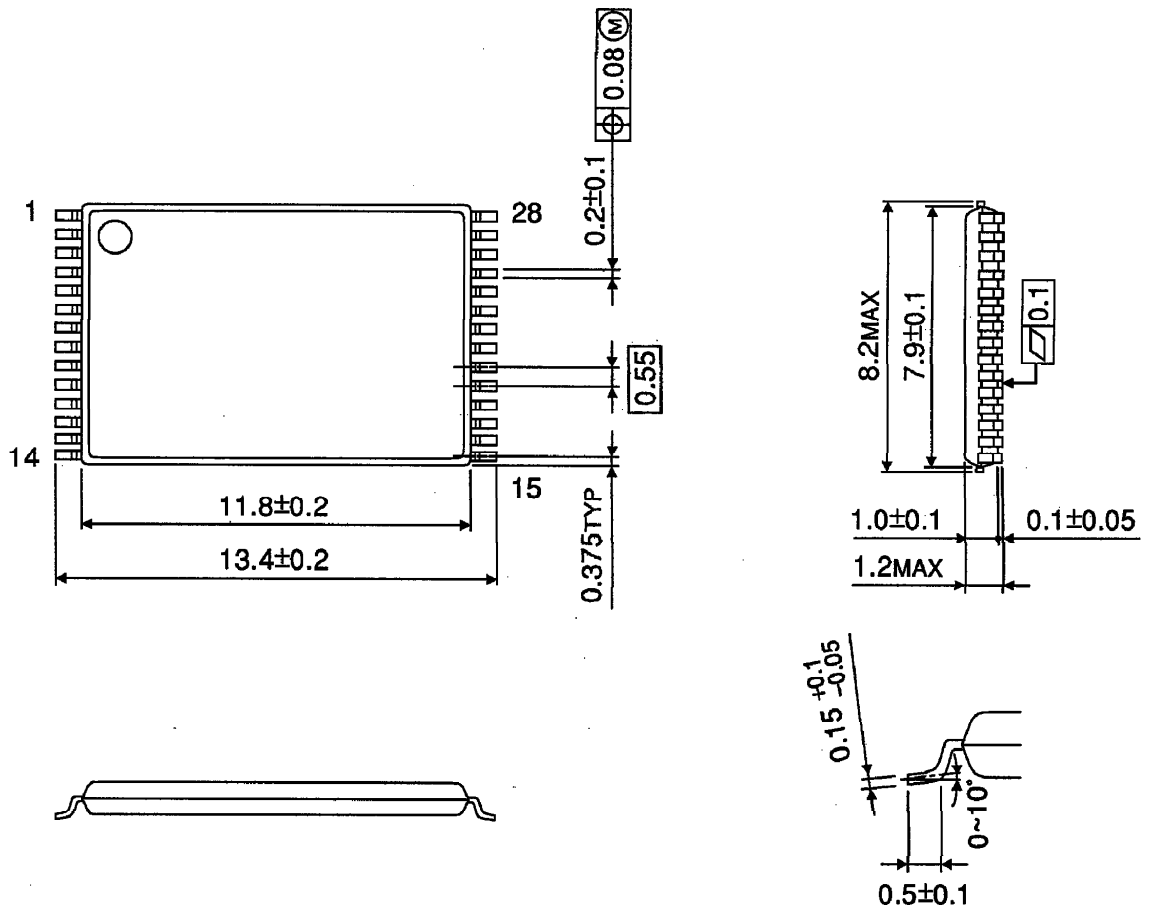
Units in mm



Weight: 0.79 g (typ)

PACKAGE DIMENSIONS (TSOP I 28-P-0.55)

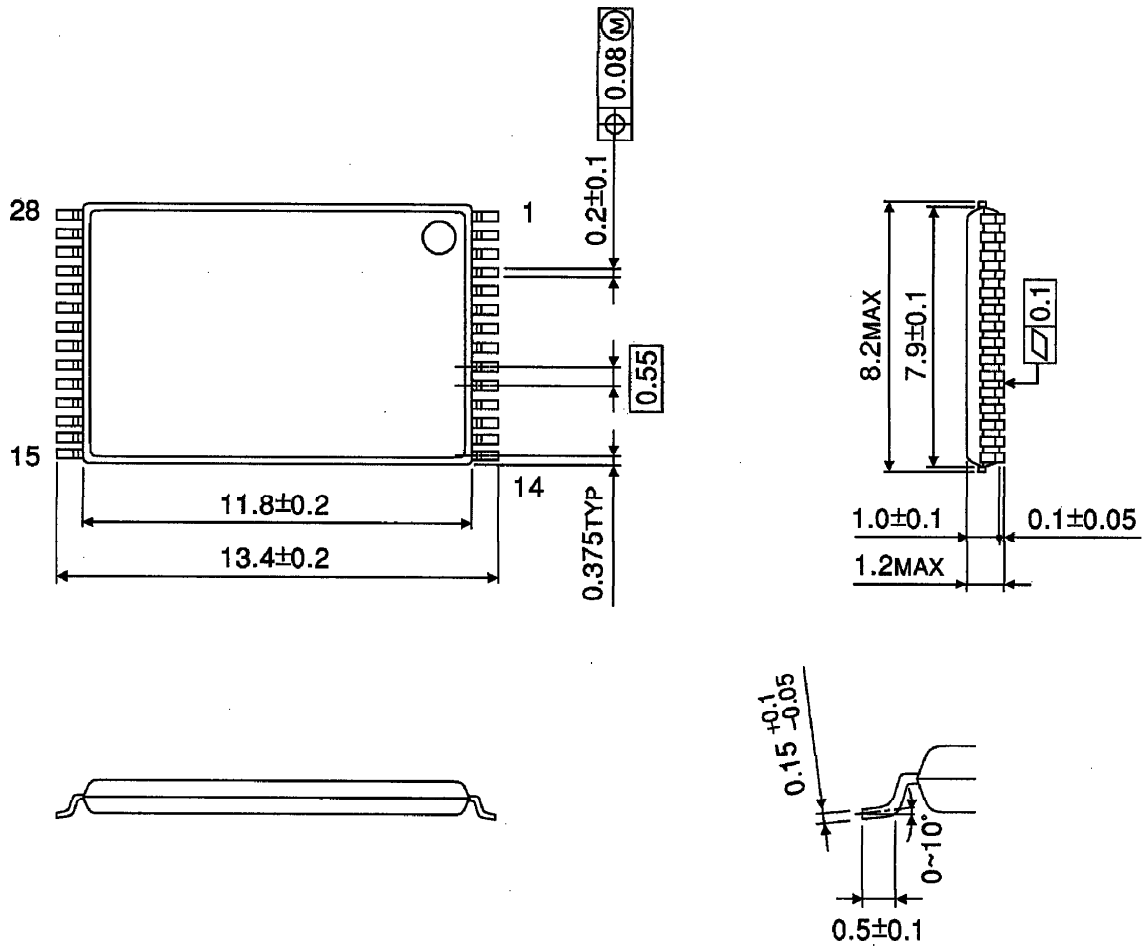
Units in mm



Weight: 0.22 g (typ)

PACKAGE DIMENSIONS (TSOP I 28-P-0.55A)

Units in mm



Weight: 0.22 g (typ)